

PHPT61010PYX Datasheet

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DiGi Electronics Part Number	PH
Manufacturer	Ne
Manufacturer Product Number	PH
Description	TR
Detailed Description	Bip

PHPT61010PYX-DG
Nexperia USA Inc.
PHPT61010PYX
TRANS PNP 100V 10A LFPAK56
Bipolar (BJT) Transistor PNP 100 V 10 A 90MHz 1.5 W Surface Mount LFPAK56, Power-S08

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PHPT61010PYX	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	10 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
100 V	800mV @ 1A, 10A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100nA	180 @ 500mA, 2V
Power - Max:	Frequency - Transition:
1.5 W	90MHz
Operating Temperature:	Grade:
175℃ (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
SC-100, SOT-669	LFPAK56, Power-SO8
Base Product Number:	
PHPT61010	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROH53 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0075	



100 V, 10 A PNP high power bipolar transistor

20 March 2015

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61010NY.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
 - High energy efficiency due to less heat generation
 - AEC-Q101 qualified

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-100	V
I _C	collector current			-	-	-10	А
I _{CM}	peak collector current	$t_p \le 1 \text{ ms}; \text{ single pulse}$		-	-	-20	А
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_C &= -10 \text{ A}; I_B = -1 \text{ A}; t_p \leq 300 \mu\text{s}; \\ \delta &\leq 0.02; T_{amb} = 25 ^\circ\text{C}; \text{ pulsed} \end{split}$		-	53	80	mΩ



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	C .
2	Е	emitter		в
3	Е	emitter	q	۲۳ ۲
4	В	base	មុប្បូប្	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PHPT61010PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT61010PY	1010PAB

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-100	V
V _{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-10	А
I _{CM}	peak collector current	$t_p \le 1 \text{ ms}$; single pulse		-	-20	Α
I _B	base current			-	-1	Α
I _{BM}	peak base current	$t_p \le 1 ms$; pulsed		-	-2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			<u>[3]</u>	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

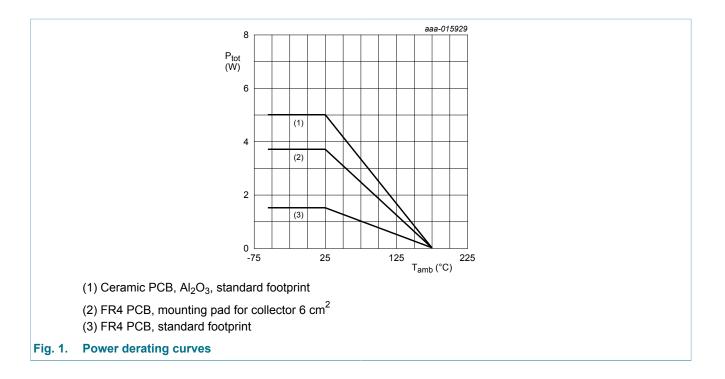
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm².

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

[4] Power dissipation from junction to mounting base.

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9. Thermal characteristics

Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
ui(j-u)	thermal resistance		[1]	-	-	100	K/W
	from junction to		[2]	-	-	41	K/W
			<u>[3]</u>	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

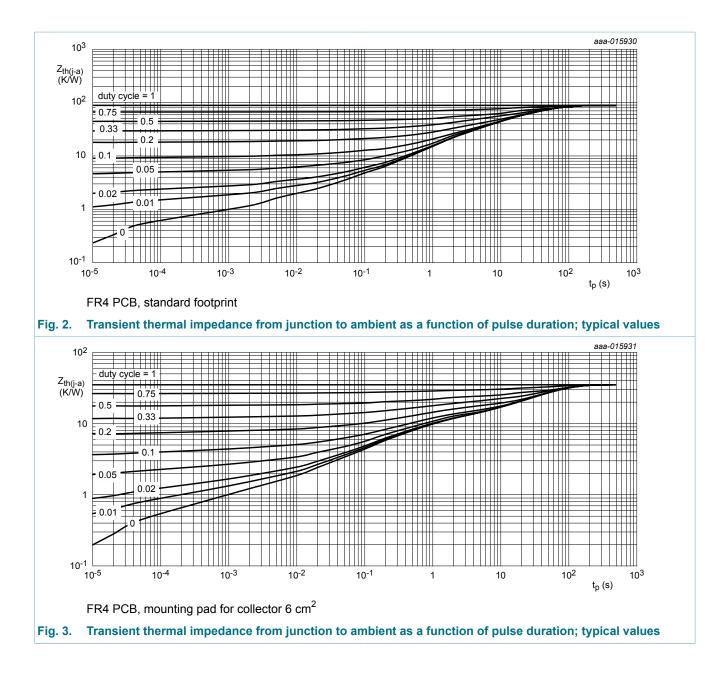
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

footprint.
 [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm².

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

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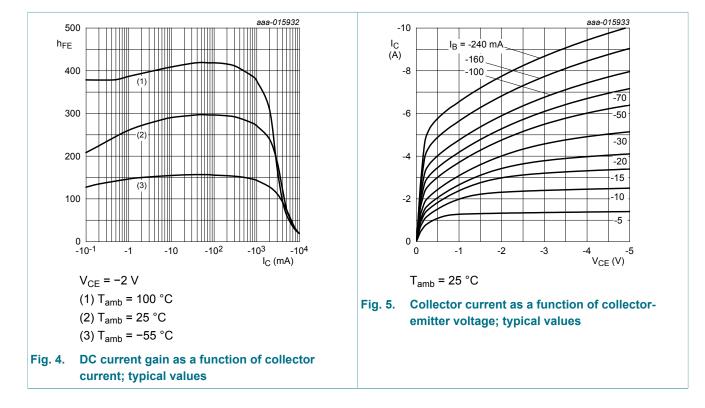
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -80 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -80 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -8 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -0.5 A; T _{amb} = 25 °C	180	330	-	
		V_{CE} = -2 V; I _C = -1 A; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C; pulsed	170	265	-	
		$V_{CE} = -2 \text{ V; } I_C = -5 \text{ A; } t_p \le 300 \mu\text{s;}$ $\delta \le 0.02; \text{ T}_{amb} = 25 ^\circ\text{C; } \text{pulsed}$	60	75	-	
		V_{CE} = -2 V; I _C = -10 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	10	15	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-55	-90	mV
		I_{C} = -5 A; I_{B} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-160	-250	mV
		I_{C} = -10 A; I_{B} = -1 A; pulsed; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-530	-800	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -10 A; I_{B} = -1 A; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	53	80	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-0.9	V
		I_{C} = -5 A; I_{B} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.1	V
		I_{C} = -10 A; I_{B} = -1 A; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-1.3	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -0.5 A; T _{amb} = 25 °C	-	-	-0.8	V
t _d	delay time	V_{CC} = -12.5 V; I _C = -5 A;	-	20	-	ns
t _r	rise time	$I_{Bon} = -250 \text{ mA}; I_{Boff} = 250 \text{ mA};$	-	145	-	ns
ton	turn-on time	T _{amb} = 25 °C	-	165	-	ns
s	storage time		-	155	-	ns
f	fall time		-	80	-	ns
t _{off}	turn-off time	-	-	235	-	ns

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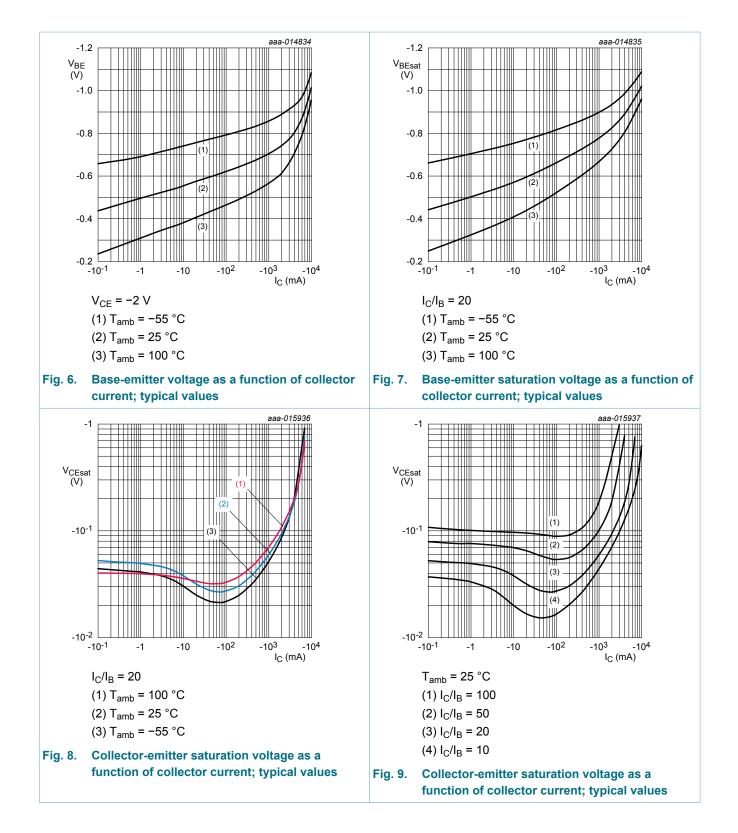
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f _T	transition frequency	V _{CE} = -10 V; I _C = -500 mA; f = 100 MHz; T _{amb} = 25 °C	-	90	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	101	-	pF



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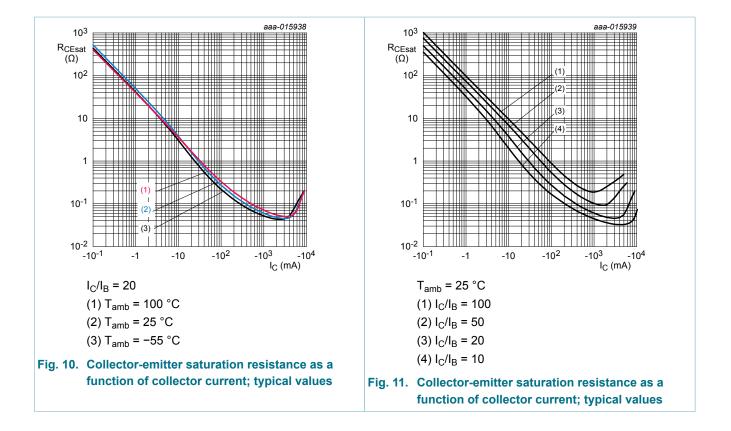


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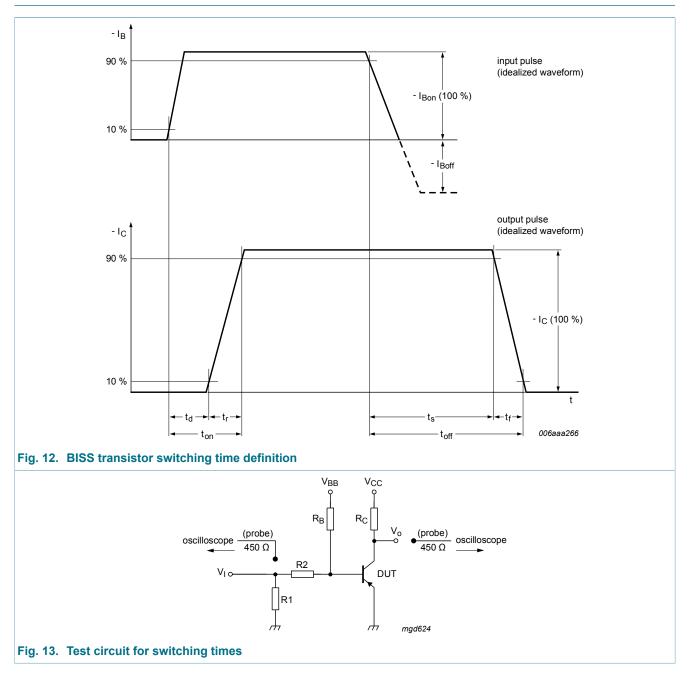
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11. Test information



11.1 Quality information

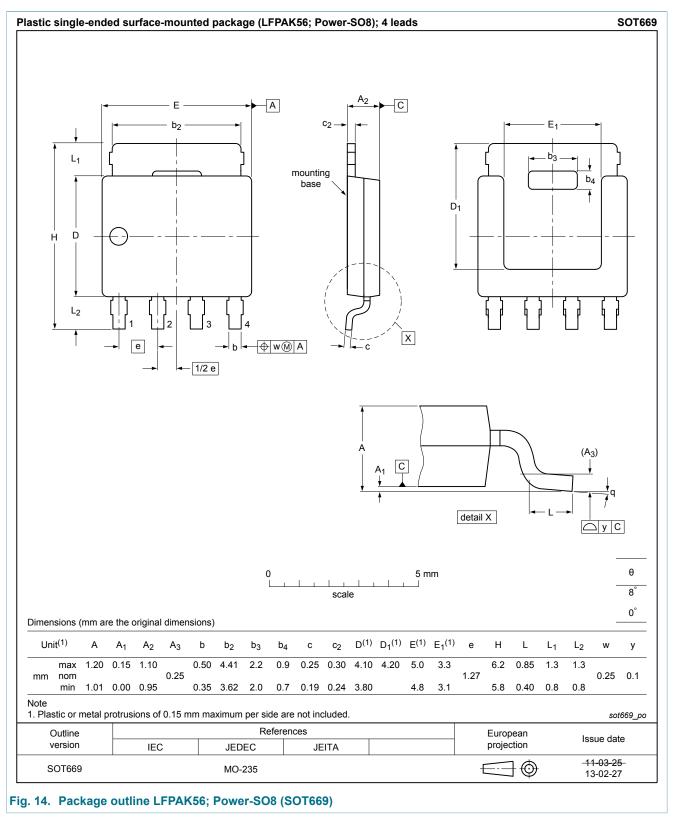
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



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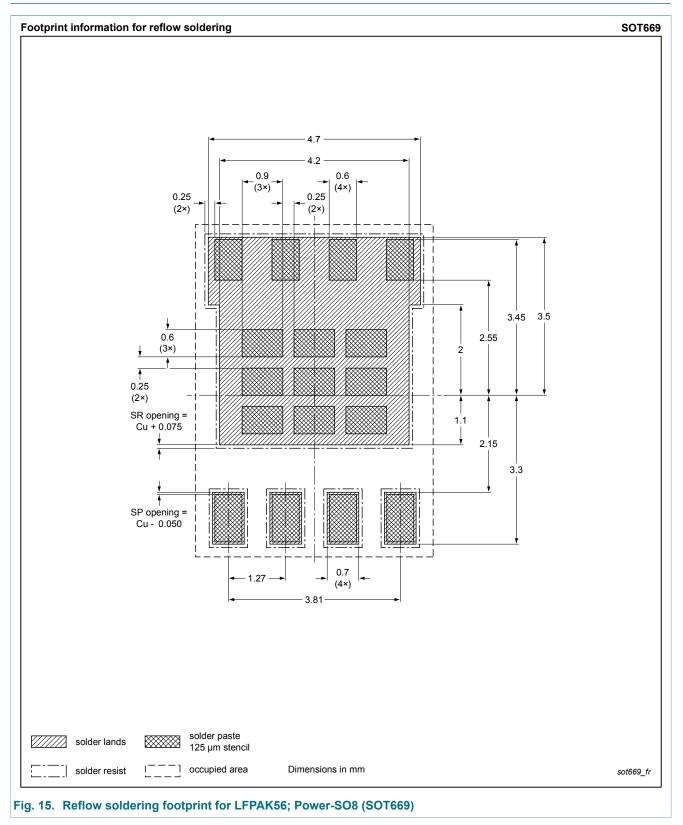
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13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT61010PY v.1	20150320	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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